RPD 装置ラインアップ

Line-up of Reactive Plasma Deposition (RPD) equipment

量産装置 (In-Line Type)
Mass Production Line
Substrate size: 550 mm×650mm
800mm×1000mm
1200mm×1800mm

RPD equipment features

- High throughput due to high deposition rate by high density arc plasma
- High quality Transparent Conductive Oxide (TCO) films can be deposited at a high deposition rate at any substrate temperature compared with conventional sputtering methods
- High availability by material supplying system without stopping deposition operation
- Low C.O.O. by low cost material and high material use efficiency
- Small foot print due to smaller number of coating sources than conventional sputtering equipments

Prototype Production Line
Substrate size: 200mm×200mm
300mm×400mm
370mm×480mm
高品質透明電極成膜を実現する RPD 装置

SUMITOMO-RPD realizes a High Quality TCO films deposition

低抵抗・高透過率 TCO 成膜
200℃以下の低温成膜条件下で、低抵抗・高透過率な TCO 成膜を実現

Low resistivity and high visible transmittance ITO or ZnO films can be deposited under low substrate temperature, e.g. below 200°C.

低ダメージ成膜プロセス
下地層に対する低ダメージ成膜が可能

RPD is a damage-free deposition method because no high energy particles (>70eV) are involved in the process.

連続真空稼働時間（実績: ～3週間）
成膜材料給供装置により、真空を維持したまま連続稼働が可能

Material supplying system realizes continuous running without maintenance for 3 weeks.

基板高速処理インラインシステム
高速成膜レートをいかした高速基板搬送技術
RPD equipment has the stable high-speed substrate conveyance system corresponding to the high deposition rate

プラズマ成膜におけるRPD法の特徴
Characteristics of the SUMITOMO-RPD as a plasma coating method

RPD-ITOとDCMS-ITOの比較
Comparison of characteristics of RPD-ITO and DCMS-ITO

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